Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	mirror adj polishing near4 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:41
S2	2	polishing near4 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 15:07
S3	5	sfqr near4 method	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:54
S4	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 15:11
S5	23	sfqr and "438"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:54
S6	4	sfqr and "438"/$7.ccls. and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55
S7	0	S6 not S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55
S8	19	S5 not S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55
S9	18	(S5 not S6) and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:56

S10	8	cmp adj polishing and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 17:15
S11	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 17:15
S12	2	polishing near4 (sfqr site adj front adj least adj square adj range)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 16:52
S13	955	mirror adj polishing.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 16:53
S14	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:11
S15	0	mirror adj polishing.ti. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:11
S16	42	method adj polishing.ti. and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:15
S17	87	method adj polishing.ti. and flatness near6 polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:27
S18	12	method adj polishing.ti. and flatness near6 polishing and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:27
S19	61	sfqr and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:42

S21	9	S19 not S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:42
S22	5	method near6 sfqr near6 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:51
S23	9	sfqr not (polish polished polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:55
S24	5	sfqr not (polish polished polishing evaluating evaluate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:56
S25	0	(growth near6 sfqr) not (polish polished polishing evaluating evaluate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S26	1	(growth near6 sfqr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S27	244	method near6 flatness near6 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S28	177	method near6 flatness near6 wafer.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58
S29	98	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58
S30	88	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing evaluat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58

S31	92	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing evaluat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/16 16:58
S32	6	"743793".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:04
S33	34	("SOI" silicon-on-insulator) and simox and wafer near6 flatness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:24
S34	0	257/347.ccls. and boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:25
S35	0	(257/34$1.ccls. 438/149.ccls.) and boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:26
S36	6	boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:34
S37	240	method near4 semiconductor adj (substrate wafer).ti,ab,clm. and "117"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:35
S38	4	"4885257".pn. "6277501".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:39
S39	2	jp-11204534$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:41
S40	2	jp-2002208596$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:42

S41	0	jp-200072595$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:43
S42	2	jp-2000072595$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:43
S43	2	jp-10229093$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:00
S44	6	"743793".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:00
S45	26	(US-20030020166-$ or US-20030227057-$ or US-20040005740-$ or US-20040031979-$ or US-20040072437-$ or US-20040135208-$).did. or (US-5474644-$ or US-5869387-$ or US-5892256-$ or US-6004866-$ or US-6090720-$ or US-6475072-$ or US-6486008-$ or US-6277501-$ or US-4885257-$).did. or (JP-2004214402-$ or JP-11204534-$ or JP-2002208596-$ or JP-2000072595-$ or JP-10229093-$).did. or (US-20040135208-$ or US-6277501-$ or DE-3427977-$ or JP-11204534-$ or JP-2002208596-$ or WO-200012787-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/06/12 22:12
S46	1	S45 and double adj side$1 adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:14
S47	55	(site adj front adj least adj square adj range sfqr) and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:16

S48	21	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:18
S49	13	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:25
S50	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron B) near3 (concentration densit$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S51	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron B) near3 (impurit$3 concentration densit$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S52	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron adj gettering (boron B) near3 (impurit$3 concentration densit$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S53	1	substrate and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron adj gettering (boron B) near3 (impurit$3 concentration densit$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S54	1	wafer and (sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron adj gettering (boron B) near3 (impurit$3 concentration densit$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:27
S55	1	(sfqr site adj front adj least adj square$1) and ("both side" double) near6 polish$3 and (boron adj gettering (boron B) near3 (impurit$3 concentration densit$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:27

S56	14	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:11
S57	0	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density)) and (two-sided "two" adj sided doubl$1) adj polish$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:12
S58	3	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density)) and ((two-sided "two" adj sided doubl$1) adj polish$3 (polish$3 near2 (front rear back back-sde))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:29
S59	0	(rms root-mean-square root adj mean adj square) near10 (sfqr site adj front adj least adj square adj range)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:17
S60	257	(boron adj gettering boron near2 (concentration impurities density)) and ((two-sided "two" adj sided doubl$1) adj polish$3 (polish$3 near2 (front rear back back-sde)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:36
S61	1	epitaxial adj wafer near10 boron near2 (concentration density) and boron adj gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37
S62	22	epitaxial adj wafer near10 boron near2 (concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37
S63	10	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37

S64	2	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:07
S65	0	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) near10 (back-side front back rear) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:41
S66	0	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) near10 (double back-side front back rear) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:41
S67	3	"2002022351".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:07
S68	2	("20020022351").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:07
S69	29	(US-20030020166-$ or US-20030227057-$ or US-20040005740-$ or US-20040031979-$ or US-20040072437-$ or US-20040135208-$ or US-20050014455-$ or US-20020022351-$ or US-20030159644-$).did. or (US-4885257-$ or US-5474644-$ or US-5869387-$ or US-5892256-$ or US-6004866-$ or US-6090720-$ or US-6277501-$ or US-6475072-$ or US-6486008-$).did. or (JP-10229093-$ or JP-11204534-$ or JP-2000072595-$ or JP-2002208596-$ or JP-2004214402-$).did. or (DE-3427977-$ or US-6277501-$ or WO-200012787-$ or JP-11204534-$ or JP-2002208596-$ or US-20040135208-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/06/13 09:13

S70	0	("L4and(siteadjfrontadjleastsfqr)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:14
S71	4	S69 and (site adj front adj least sfqr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:22
S73	0	surface adj roughness near4 compressibility near10 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:23
S74	3	sfqr near6 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:47
S75	174	boron adj concentration near6 thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:48
S76	1	boron adj concentration near6 thickness and S69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:59
S77	0	boron adj concentration near6 "exp"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:15
S78	0	"SOI" and SIMO and (Si near3 SiGe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:16
S79	1079	"SOI" and (Si near3 SiGe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:16
S80	25	"SOI" and (Si near3 SiGe) near6 stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:46

S81	2	"SOI" and back adj shield near10 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:48
S82	18	"SOI" and rear near10 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:50
S83	476	"SOI" and exposed near6 (back back-side rear)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:50
S84	230	"SOI" and exposed near3 (back back-side rear)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:59
S85	19	"SOI" and exposed near3 (back back-side rear).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:03
S86	116	"SIO" and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:06
S87	94	"SIO".ti,ab,clm. and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:07
S88	4	"SOI".ti,ab,clm. and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:07
S89	0	("tanahashi.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:31
S90	4146	tanahashi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:31

S91	1	tanahashi.in. and boron and substrate and "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:32
S92	1	tanahashi.in. and boron and substrate and concentration.clm. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:32
S93	1	tanahashi.in. and boron and substrate and concentration.clm. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:33
S94	1	boron adj gettering and "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:37
S95	5410	((257/347) or (257/348) or (257/349) or (257/35$1) or (257/e29.105) or (257/e29.106) or (257/e29.108) or (257/e21.135) or (257/913)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/13 11:38
S96	0	S95 and boron adj concentration and "SOI" and boron adj gettering and exposed near6 (rear back back-side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:39
S97	6	"743793".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/28 07:30
S98	1	(US-20040135208-$).did.	US-PGPUB	OR	OFF	2005/12/28 07:38
S99	2	("20030159644").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/28 07:40
S100	1	S99 and (thick thickness) near4 epitaxial	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/28 07:46
S101	1	S99 and (thick thickness) near4 epitaxial and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:29

S10 2	0	(polished near2 mirror) near6 rear near6 oxide near6 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:30
S10 3	0	(polished near2 mirror) near6 (back rear rearside backside) near6 oxide near6 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:31
S10 4	0	(polished near6 mirror) near6 (back rear rearside backside) near6 oxide near6 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:31
S10 5	10	(polished near8 mirror) near8 (back rear rearside backside) near8 (expos$3 oxide near6 nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:34
S10 6	9	(polished near8 mirror) near8 (back rear rearside backside) near8 (expos$3 oxide near6 nm) and mirror near1 polish$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 11:54
S10 7	5131	((257/347) or (257/348) or (257/349) or (257/350) or (257/351) or (257/352) or (257/353) or (257/354) or (257/368) or (257/607) or (257/e29.105) or (257/e29.106) or (257/e21.135) or (257/913)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/12/28 11:55
S10 8	9	S107 and mirror near4 polish$3 and (wafer substrate) and (flatness atomically near1 flat sfqr "R.max.") and (boron near6 density concentration abundance) and (epitaxy epitaxial epitaxially) and (crystalline monocrystal monocrystalline single adj crystal) and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 12:01
S10 9	9	S107 and mirror near4 polish$3 and (wafer substrate) and (flatness atomically near1 flat sfqr "R.max.") and (boron near6 density concentration abundance) and (epitaxy epitaxial epitaxially) and (crystalline monocrystal monocrystalline single adj crystal) near6 (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 12:01